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Understanding Embedded - Microprocessors

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Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	533MHz
Co-Processors/DSP	Security; SEC
RAM Controllers	DDR
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (2)
Voltage - I/O	2.5V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	Cryptography, Random Number Generator
Package / Case	672-LBGA
Supplier Device Package	672-LBGA (35x35)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8347ecvvajdb

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



NOTE

The information in this document is accurate for revision 3.x silicon and later (in other words, for orderable part numbers ending in A or B). For information on revision 1.1 silicon and earlier versions, see the *MPC8347E PowerQUICC II Pro Integrated Host Processor Hardware Specifications*.

See Section 22.1, "Part Numbers Fully Addressed by This Document," for silicon revision level determination.

1 Overview

This section provides a high-level overview of the device features. Figure 1 shows the major functional units within the MPC8347EA.

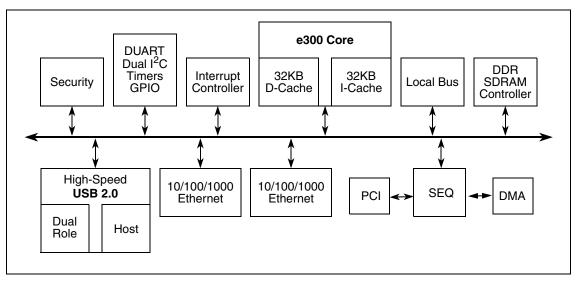


Figure 1. MPC8347EA Block Diagram

Major features of the device are as follows:

- Embedded PowerPC e300 processor core; operates at up to 667 MHz
 - High-performance, superscalar processor core
 - Floating-point, integer, load/store, system register, and branch processing units
 - 32-Kbyte instruction cache, 32-Kbyte data cache
 - Lockable portion of L1 cache
 - Dynamic power management
 - Software-compatible with the other Freescale processor families that implement Power Architecture technology
- Double data rate, DDR1/DDR2 SDRAM memory controller
 - Programmable timing supporting DDR1 and DDR2 SDRAM
 - 32- or 64-bit data interface, up to 400 MHz data rate for TBGA, 266 MHz for PBGA



Power Characteristics

supplies are stable and if the I/O voltages are supplied before the core voltage, there may be a period of time that all input and output pins will actively be driven and cause contention and excessive current from 3A to 5A. In order to avoid actively driving the I/O pins and to eliminate excessive current draw, apply the core voltage (V_{DD}) before the I/O voltage (GV_{DD} , LV_{DD} , and OV_{DD}) and assert PORESET before the power supplies fully ramp up. In the case where the core voltage is applied first, the core voltage supply must rise to 90% of its nominal value before the I/O supplies reach 0.7 V, see Figure 4.

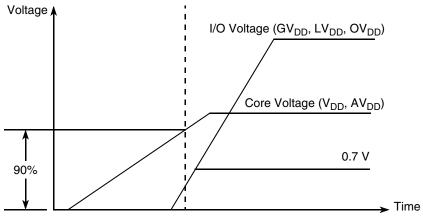


Figure 4. Power Sequencing Example

I/O voltage supplies (GV_{DD} , LV_{DD} , and OV_{DD}) do not have any ordering requirements with respect to one another.

3 Power Characteristics

The estimated typical power dissipation for the MPC8347EA device is shown in Table 4.

	Core Frequency (MHz)	CSB Frequency (MHz)	Typical at T _J = 65	Typical ^{2,3}	Maximum ⁴	Unit
PBGA	266	266	1.3	1.6	1.8	W
		133	1.1	1.4	1.6	W
	400	266	1.5	1.9	2.1	W
		133	1.4	1.7	1.9	W
	400	200	1.5	1.8	2.0	W
		100	1.3	1.7	1.9	W

Table 4. MPC8347EA Power Dissipation¹



Table 12. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V (continued)

Output low current ($V_{OUT} = 0.280 V$) I_{OL} 13.4mA
--

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.

2. MV_{REF} is expected to equal 0.5 × GV_{DD} , and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} cannot exceed ±2% of the DC value.

 V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to equal MV_{REF}. This rail should track variations in the DC level of MV_{REF}.

4. Output leakage is measured with all outputs disabled, 0 V \leq V_{OUT} \leq GV_{DD}.

Table 13 provides the DDR2 capacitance when $GV_{DD}(typ) = 1.8$ V.

Table 13. DDR2 SDRAM Capacitance for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, DQS	C _{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS, DQS	C _{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. $GV_{DD} = 1.8 \text{ V} \pm 0.090 \text{ V}$, f = 1 MHz, T_A = 25°C, V_{OUT} = $GV_{DD}/2$, V_{OUT} (peak-to-peak) = 0.2 V.

Table 14 provides the recommended operating conditions for the DDR SDRAM component(s) when $GV_{DD}(typ) = 2.5 \text{ V}.$

Table 14. DDR SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 2.5 V

Parameter/Condition	Symbol	Min	Мах	Unit	Notes
I/O supply voltage	GV _{DD}	2.375	2.625	V	1
I/O reference voltage	MV _{REF}	$0.49 imes GV_{DD}$	$0.51 imes GV_{DD}$	V	2
I/O termination voltage	V _{TT}	MV _{REF} – 0.04	MV _{REF} + 0.04	V	3
Input high voltage	V _{IH}	MV _{REF} + 0.18	GV _{DD} + 0.3	V	—
Input low voltage	V _{IL}	-0.3	MV _{REF} – 0.18	V	—
Output leakage current	I _{OZ}	-9.9	-9.9	μA	4
Output high current (V _{OUT} = 1.95 V)	I _{OH}	-15.2	—	mA	
Output low current (V _{OUT} = 0.35 V)	I _{OL}	15.2	—	mA	—

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.

 MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.

3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.

4. Output leakage is measured with all outputs disabled, 0 V \leq V_{OUT} \leq GV_{DD}.



DDR and DDR2 SDRAM

6.2.2 DDR and DDR2 SDRAM Output AC Timing Specifications

Table 20 shows the DDR and DDR2 output AC timing specifications.

Table 20. DDR and DDR2 SDRAM Output AC Timing Specifications

At recommended operating conditions with GV_{DD} of (1.8 or 2.5 V) \pm 5%.

Parameter	Symbol ¹	Min	Max	Unit	Notes
MCK[n] cycle time, (MCK[n]/MCK[n] crossing) (PBGA package)	t _{MCK}	5	_	ns	2
MCK[n] cycle time, (MCK[n]/MCK[n] crossing) (TBGA package)	t _{MCK}	7.5	—	ns	2
ADDR/CMD/MODT output setup with respect to MCK	t _{DDKHAS}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	—		
200 MHz		4.20	_		
ADDR/CMD/MODT output hold with respect to MCK	t _{DDKHAX}			ns	3
400 MHz		1.95	_		
333 MHz		2.40	_		
266 MHz		3.15	_		
200 MHz		4.20	_		
MCS(n) output setup with respect to MCK	t _{DDKHCS}			ns	3
400 MHz		1.95	_		
333 MHz		2.40	_		
266 MHz		3.15	_		
200 MHz		4.20	_		
MCS(n) output hold with respect to MCK	t _{DDKHCX}			ns	3
400 MHz		1.95	—		
333 MHz		2.40	—		
266 MHz		3.15	_		
200 MHz		4.20	_		
MCK to MDQS Skew	t _{DDKHMH}	-0.6	0.6	ns	4
MDQ/MECC/MDM output setup with respect to MDQS	t _{DDKHDS,} t _{DDKLDS}			ps	5
400 MHz		700	—		
333 MHz		775	—		
266 MHz		1100	—		
200 MHz		1200	—		
MDQ/MECC/MDM output hold with respect to MDQS	t _{DDKHDX,} t _{DDKLDX}			ps	5
400 MHz		700	—		
333 MHz		900	—		



Figure 7 shows the DDR SDRAM output timing diagram.

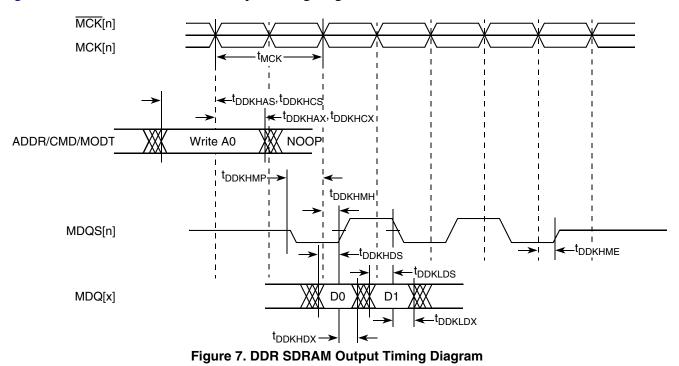


Figure 8 provides the AC test load for the DDR bus.

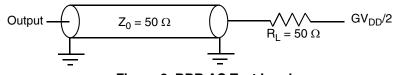


Figure 8. DDR AC Test Load

7 DUART

This section describes the DC and AC electrical specifications for the DUART interface of the MPC8347EA.

7.1 DUART DC Electrical Characteristics

Table 21 provides the DC electrical characteristics for the DUART interface of the MPC8347EA.

Table 21. DUART DC Electrical Characteristics

Parameter	Symbol	Min	Мах	Unit
High-level input voltage	V _{IH}	2	OV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.8	V
Input current (0.8 V \leq V _{IN} \leq 2 V)	I _{IN}	—	±5	μA



8.2.3.1 TBI Transmit AC Timing Specifications

Table 29 provides the TBI transmit AC timing specifications.

Table 29. TBI Transmit AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
GTX_CLK clock period	t _{TTX}	—	8.0	—	ns
GTX_CLK duty cycle	t _{TTXH} /t _{TTX}	40	_	60	%
GTX_CLK to TBI data TXD[7:0], TX_ER, TX_EN delay	t _{TTKHDX}	1.0	_	5.0	ns
GTX_CLK clock rise (20%–80%)	t _{TTXR}	_	_	1.0	ns
GTX_CLK clock fall time (80%–20%)	t _{TTXF}	—		1.0	ns

Notes:

1. The symbols for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{TTKHDV} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (V) or setup time. Also, t_{TTKHDX} symbolizes the TBI transmit timing (TT) with respect to the time from t_{TTX} (K) going high (H) until the referenced data signals (D) reach the valid state (X) or hold time. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{TTX} represents the TBI (T) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).}}

Figure 14 shows the TBI transmit AC timing diagram.

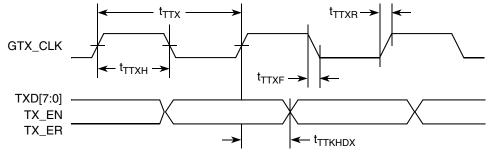


Figure 14. TBI Transmit AC Timing Diagram

8.2.3.2 TBI Receive AC Timing Specifications

Table 30 provides the TBI receive AC timing specifications.

Table 30. TBI Receive AC Timing Specifications

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V ± 10%.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
PMA_RX_CLK clock period	t _{TRX}		16.0		ns
PMA_RX_CLK skew	t _{SKTRX}	7.5	—	8.5	ns
RX_CLK duty cycle	t _{TRXH} /t _{TRX}	40		60	%



Ethernet: Three-Speed Ethernet, MII Management

Table 30. TBI Receive AC Timing Specifications (continued)

At recommended operating conditions with LV_{DD}/OV_{DD} of 3.3 V \pm 10%.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
RXD[7:0], RX_DV, RX_ER (RCG[9:0]) setup time to rising PMA_RX_CLK	t _{TRDVKH} ²	2.5	—	—	ns
RXD[7:0], RX_DV, RX_ER (RCG[9:0]) hold time to rising PMA_RX_CLK	t _{TRDXKH} 2	1.5	—	—	ns
RX_CLK clock rise time (20%–80%)	t _{TRXR}	0.7	—	2.4	ns
RX_CLK clock fall time (80%–20%)	t _{TRXF}	0.7	—	2.4	ns

Notes:

The symbols for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{TRDVKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{TRX} clock reference (K) going to the high (H) state or setup time. Also, t_{TRDXKH} symbolizes TBI receive timing (TR) with respect to the time data input signals (D) went invalid (X) relative to the t_{TRX} clock reference (K) going to the high (H) state. In general, the clock reference symbol is based on three letters representing the clock of a particular function. For example, the subscript of t_{TRX} represents the TBI (T) receive (RX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall). For symbols representing skews, the subscript SK followed by the clock that is being skewed (TRX).
</sub>

2. Setup and hold time of even numbered RCG are measured from the riding edge of PMA_RX_CLK1. Setup and hold times of odd-numbered RCG are measured from the riding edge of PMA_RX_CLK0.

Figure 15 shows the TBI receive AC timing diagram.

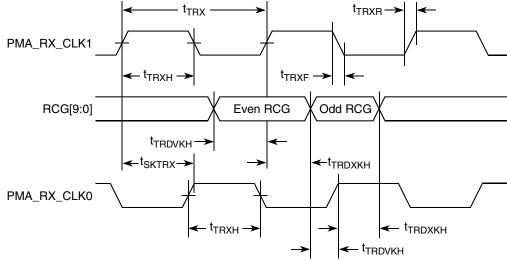


Figure 15. TBI Receive AC Timing Diagram



8.2.4 RGMII and RTBI AC Timing Specifications

Table 31 presents the RGMII and RTBI AC timing specifications.

Table 31. RGMII and RTBI AC Timing Specifications

At recommended operating conditions with LV_{DD} of 2.5 V ± 5%.

Parameter/Condition	Symbol ¹	Min	Тур	Max	Unit
Data to clock output skew (at transmitter)	t _{SKRGT}	-0.5		0.5	ns
Data to clock input skew (at receiver) ²	t _{SKRGT}	1.0	—	2.8	ns
Clock cycle duration ³	t _{RGT}	7.2	8.0	8.8	ns
Duty cycle for 1000Base-T ^{4, 5}	t _{RGTH} /t _{RGT}	45	50	55	%
Duty cycle for 10BASE-T and 100BASE-TX ^{3, 5}	t _{RGTH} /t _{RGT}	40	50	60	%
Rise time (20%–80%)	t _{RGTR}	_	—	0.75	ns
Fall time (80%–20%)	t _{RGTF}			0.75	ns

Notes:

1. In general, the clock reference symbol for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Also, the notation for rise (R) and fall (F) times follows the clock symbol. For symbols representing skews, the subscript is SK followed by the clock being skewed (RGT).

2. This implies that PC board design requires clocks to be routed so that an additional trace delay of greater than 1.5 ns is added to the associated clock signal.

3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns \pm 40 ns and 40 ns \pm 4 ns, respectively.

4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned.

5. Duty cycle reference is $LV_{DD}/2$.



9 USB

This section provides the AC and DC electrical specifications for the USB interface of the MPC8347EA.

9.1 USB DC Electrical Characteristics

Table 35 provides the DC electrical characteristics for the USB interface.

Table 35	. USB DC	Electrical	Characteristics
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Parameter	Symbol	Min	Мах	Unit
High-level input voltage	V _{IH}	2	OV _{DD} + 0.3	V
Low-level input voltage	V _{IL}	-0.3	0.8	V
Input current	I _{IN}	—	±5	μA
High-level output voltage, $I_{OH} = -100 \ \mu A$	V _{OH}	OV _{DD} - 0.2	—	V
Low-level output voltage, $I_{OL} = 100 \ \mu A$	V _{OL}	—	0.2	V

9.2 USB AC Electrical Specifications

Table 36 describes the general timing parameters of the USB interface of the MPC8347EA.

Table 36. USB General Timing Parameters (ULPI Mode Only)

Parameter	Symbol ¹	Min	Мах	Unit	Notes
USB clock cycle time	t _{USCK}	15	—	ns	2–5
Input setup to USB clock—all inputs	t _{USIVKH}	4	—	ns	2–5
Input hold to USB clock—all inputs	t _{USIXKH}	1	—	ns	2–5
USB clock to output valid—all outputs	t _{USKHOV}	—	7	ns	2–5
Output hold from USB clock—all outputs	t _{USKHOX}	2	—	ns	2–5

Notes:

 The symbols for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state)} for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{USIXKH} symbolizes USB timing (US) for the input (I) to go invalid (X) with respect to the time the USB clock reference (K) goes high (H). Also, t_{USKHOX} symbolizes USB timing (US) for the USB clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.

2. All timings are in reference to USB clock.

3. All signals are measured from $OV_{DD}/2$ of the rising edge of the USB clock to $0.4 \times OV_{DD}$ of the signal in question for 3.3 V signaling levels.

4. Input timings are measured at the pin.

5. For active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to that of the leakage current specification.

Parameter	Symbol ¹	Min	Мах	Unit	Notes
Local bus cycle time	t _{LBK}	15	—	ns	2
Input setup to local bus clock	t _{LBIVKH}	7	—	ns	3, 4
Input hold from local bus clock	t _{LBIXKH}	1.0	—	ns	3, 4
LALE output fall to LAD output transition (LATCH hold time)	t _{LBOTOT1}	1.5	—	ns	5
LALE output fall to LAD output transition (LATCH hold time)	t _{LBOTOT2}	3	—	ns	6
LALE output fall to LAD output transition (LATCH hold time)	t _{LBOTOT3}	2.5	—	ns	7
Local bus clock to output valid	t _{LBKLOV}	—	3	ns	3
Local bus clock to output high impedance for LAD/LDP	t _{LBKHOZ}	—	4	ns	8

Table 39. Local Bus General Timing Parameters—DLL Bypass⁹

Notes:

The symbols for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_(first two letters of functional block)(reference)(state)(signal)(state) for outputs. For example, t_{LBIXKH1} symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one (1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
</sub>

- 2. All timings are in reference to the falling edge of LCLK0 (for all outputs and for LGTA and LUPWAIT inputs) or the rising edge of LCLK0 (for all other inputs).
- 3. All signals are measured from $OV_{DD}/2$ of the rising/falling edge of LCLK0 to $0.4 \times OV_{DD}$ of the signal in question for 3.3 V signaling levels.
- 4. Input timings are measured at the pin.
- 5. t_{LBOTOT1} should be used when RCWH[LALE] is set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.
- 6. t_{LBOTOT2} should be used when RCWH[LALE] is not set and when the load on the LALE output pin is at least 10 pF less than the load on the LAD output pins.the
- 7. t_{LBOTOT3} should be used when RCWH[LALE] is not set and when the load on the LALE output pin equals to the load on the LAD output pins.
- 8. For purposes of active/float timing measurements, the Hi-Z or off-state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
- 9. DLL bypass mode is not recommended for use at frequencies above 66 MHz.

Figure 20 provides the AC test load for the local bus.

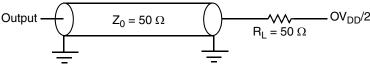


Figure 20. Local Bus C Test Load

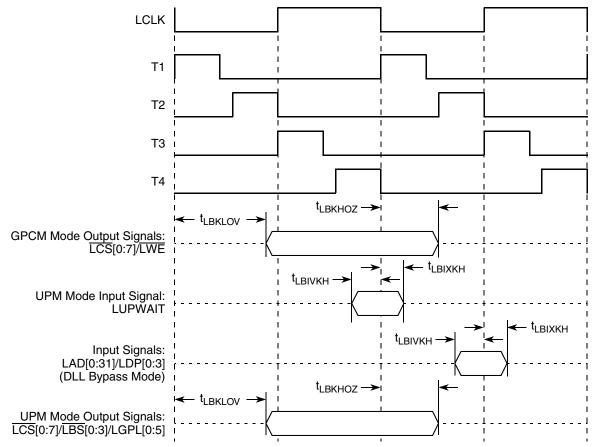


Figure 25. Local Bus Signals, GPCM/UPM Signals for LCCR[CLKDIV] = 4 (DLL Bypass Mode)



Figure 35 shows the PCI input AC timing diagram.

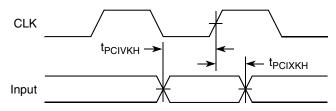
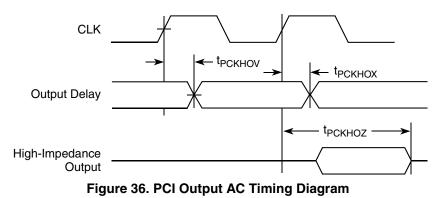


Figure 35. PCI Input AC Timing Diagram

Figure 36 shows the PCI output AC timing diagram.



14 Timers

This section describes the DC and AC electrical specifications for the timers.

14.1 Timer DC Electrical Characteristics

Table 47 provides the DC electrical characteristics for the MPC8347EA timer pins, including TIN, $\overline{\text{TOUT}}$, TGATE, and RTC_CLK.

Parameter	Symbol	Condition	Min	Мах	Unit
Input high voltage	V _{IH}	—	2.0	OV _{DD} + 0.3	V
Input low voltage	V _{IL}	—	-0.3	0.8	V
Input current	I _{IN}	—	—	±5	μA
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	—	V
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	—	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	—	0.4	V

Table 47. Timer DC Electrical Characteristics



Parameter	Symbol	Condition	Min	Мах	Unit
Input current	I _{IN}	_	_	±5	μA
Output high voltage	V _{OH}	I _{OH} = -8.0 mA	2.4	_	V
Output low voltage	V _{OL}	I _{OL} = 8.0 mA	_	0.5	V
Output low voltage	V _{OL}	I _{OL} = 3.2 mA	_	0.4	V

Table 53. SPI DC Electrical Characteristics (continued)

17.2 SPI AC Timing Specifications

Table 54 provides the SPI input and output AC timing specifications.

Table 54.	SPI AC T	iming S	pecifications ¹
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Parameter	Symbol ²	Min	Мах	Unit
SPI outputs valid—Master mode (internal clock) delay	t _{NIKHOV}	—	6	ns
SPI outputs hold—Master mode (internal clock) delay	t _{NIKHOX}	0.5	—	ns
SPI outputs valid—Slave mode (external clock) delay	t _{NEKHOV}	—	8	ns
SPI outputs hold—Slave mode (external clock) delay	t _{NEKHOX}	2	—	ns
SPI inputs—Master mode (internal clock input setup time	t _{NIIVKH}	4	—	ns
SPI inputs—Master mode (internal clock input hold time	t _{NIIXKH}	0	_	ns
SPI inputs—Slave mode (external clock) input setup time	t _{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t _{NEIXKH}	2	—	ns

Notes:

1. Output specifications are measured from the 50 percent level of the rising edge of CLKIN to the 50 percent level of the signal. Timings are measured at the pin.

The symbols for timing specifications follow the pattern of t_{(first two letters of functional block)(signal)(state)(reference)(state)} for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{NIKHOX} symbolizes the internal timing (NI) for the time SPICLK clock reference (K) goes to the high state (H) until outputs (O) are invalid (X).

Figure 37 provides the AC test load for the SPI.

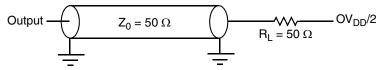


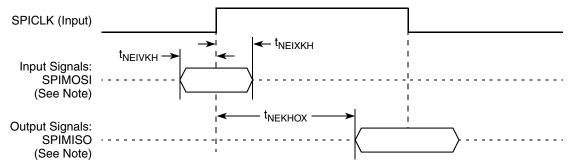
Figure 37. SPI AC Test Load



Package and Pin Listings

Figure 38 and Figure 39 represent the AC timings from Table 54. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

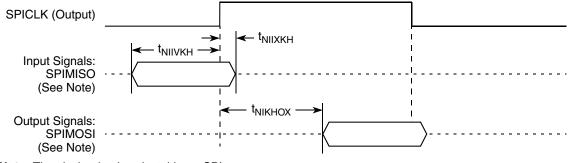
Figure 38 shows the SPI timings in slave mode (external clock).



Note: The clock edge is selectable on SPI.

Figure 38. SPI AC Timing in Slave Mode (External Clock) Diagram

Figure 39 shows the SPI timings in master mode (internal clock).



Note: The clock edge is selectable on SPI.



18 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8347EA is available in two packages—a tape ball grid array (TBGA) and a plastic ball grid array (PBGA). See Section 18.1, "Package Parameters for the MPC8347EA TBGA," Section 18.2, "Mechanical Dimensions for the MPC8347EA TBGA," Section 18.3, "Package Parameters for the MPC8347EA PBGA," and Section 18.4, "Mechanical Dimensions for the MPC8347EA PBGA."

18.1 Package Parameters for the MPC8347EA TBGA

The package parameters are provided in the following list. The package type is $35 \text{ mm} \times 35 \text{ mm}$, 672 tape ball grid array (TBGA).

Package outline	$35 \text{ mm} \times 35 \text{ mm}$
Interconnects	672



18.5 Pinout Listings

Table 55 provides the pinout listing for the MPC8347EA, 672 TBGA package.

Table 55. MPC8347EA (TBGA) Pinout Listing

Signal	Package Pin Number	Pin Type	Power Supply	Notes
	PCI		1	•
PCI_INTA/IRQ_OUT	B34	0	OV _{DD}	2
PCI_RESET_OUT	C33	0	OV _{DD}	_
PCI_AD[31:0]	G30, G32, G34, H31, H32, H33, H34, J29, J32, J33, L30, K31, K33, K34, L33, L34, P34, R29, R30, R33, R34, T31, T32, T33, U31, U34, V31, V32, V33, V34, W33, W34	I/O	OV _{DD}	_
PCI_C/BE[3:0]	J30, M31, P33, T34	I/O	OV _{DD}	—
PCI_PAR	P32	I/O	OV _{DD}	—
PCI_FRAME	M32	I/O	OV _{DD}	5
PCI_TRDY	N29	I/O	OV _{DD}	5
PCI_IRDY	M34	I/O	OV _{DD}	5
PCI_STOP	N31	I/O	OV _{DD}	5
PCI_DEVSEL	N30	I/O	OV _{DD}	5
PCI_IDSEL	J31	I	OV _{DD}	—
PCI_SERR	N34	I/O	OV _{DD}	5
PCI_PERR	N33	I/O	OV _{DD}	5
PCI_REQ[0]	D32	I/O	OV _{DD}	—
PCI_REQ[1]/CPCI1_HS_ES	D34	I	OV _{DD}	—
PCI_REQ[2:4]	E34, F32, G29	Ι	OV _{DD}	—
PCI_GNT0	C34	I/O	OV _{DD}	_
PCI_GNT1/CPCI1_HS_LED	D33	0	OV _{DD}	_
PCI_GNT2/CPCI1_HS_ENUM	E33	0	OV _{DD}	—
PCI_GNT[3:4]	F31, F33	0	OV _{DD}	—
M66EN	A19	I	OV _{DD}	—
	DDR SDRAM Memory Interface			•
MDQ[0:63]	D5, A3, C3, D3, C4, B3, C2, D4, D2, E5, G2, H6, E4, F3, G4, G3, H1, J2, L6, M6, H2, K6, L2, M4, N2, P4, R2, T4, P6, P3, R1, T2, AB5, AA3, AD6, AE4, AB4, AC2, AD3, AE6, AE3, AG4, AK5, AK4, AE2, AG6, AK3, AK2, AL2, AL1, AM5, AP5, AM2, AN1, AP4, AN5, AJ7, AN7, AM8, AJ9, AP6, AL7, AL9, AN8	I/O	GV _{DD}	



Package and Pin Listings

Table 55. MPC8347EA (TBGA) Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
TSEC2_TXD[3:0]/GPIO1[17:20]	B5, A5, F8, B6	I/O	LV _{DD2}	—
TSEC2_TX_ER/GPIO1[24]	F14	I/O	OV _{DD}	—
TSEC2_TX_EN/GPIO1[12]	C5	I/O	LV _{DD2}	3
TSEC2_TX_CLK/GPIO1[30]	E14	I/O	OV _{DD}	—
	DUART	I	1	
UART_SOUT[1:2]/MSRCID[0:1]/LSRCID[0:1]	AK27, AN29	0	OV _{DD}	_
UART_SIN[1:2]/MSRCID[2:3]/LSRCID[2:3]	AL28, AM29	I/O	OV _{DD}	—
UART_CTS[1]/MSRCID4/LSRCID4	AP30	I/O	OV _{DD}	—
UART_CTS[2]/MDVAL/ LDVAL	AN30	I/O	OV _{DD}	—
UART_RTS[1:2]	AP31, AM30	0	OV _{DD}	
	I ² C interface	Ι		1
IIC1_SDA	AK29	I/O	OV _{DD}	2
IIC1_SCL	AP32	I/O	OV _{DD}	2
IIC2_SDA	AN31	I/O	OV _{DD}	2
IIC2_SCL	AM31	I/O	OV _{DD}	2
	SPI	I	_	1
SPIMOSI/LCS[6]	AN32	I/O	OV _{DD}	—
SPIMISO/LCS[7]	AP33	I/O	OV _{DD}	—
SPICLK	AK30	I/O	OV _{DD}	
SPISEL	AL31	I	OV _{DD}	—
	Clocks	I	1	
PCI_CLK_OUT[0:2]	AN9, AP9, AM10	0	OV _{DD}	—
PCI_CLK_OUT[3]/LCS[6]	AN10	0	OV _{DD}	—
PCI_CLK_OUT[4]/LCS[7]	AJ11	0	OV _{DD}	—
PCI_SYNC_IN/PCI_CLOCK	AK12	I	OV _{DD}	—
PCI_SYNC_OUT	AP11	0	OV _{DD}	3
RTC/PIT_CLOCK	AM32	I	OV _{DD}	—
CLKIN	AM9	I	OV _{DD}	
	JTAG	I	_	1
ТСК	E20	I	OV _{DD}	_
TDI	F20	I	OV _{DD}	4
TDO	B20	0	OV _{DD}	3
TMS	A20	I	OV _{DD}	4
TRST	B19	I	OV _{DD}	4



Package and Pin Listings

Signal	Package Pin Number	Pin Type	Power Supply	Notes
	I ² C interface			
IIC1_SDA	E5	I/O	OV _{DD}	2
IIC1_SCL	A6	I/O	OV _{DD}	2
IIC2_SDA	B6	I/O	OV _{DD}	2
IIC2_SCL	E7	I/O	OV _{DD}	2
	SPI		•	
SPIMOSI/LCS[6]	D7	I/O	OV _{DD}	_
SPIMISO/LCS[7]	C7	I/O	OV _{DD}	—
SPICLK	B7	I/O	OV _{DD}	—
SPISEL	A7	I	OV _{DD}	—
	Clocks		1	
PCI_CLK_OUT[0:2]	Y1, W3, W2	0	OV _{DD}	_
PCI_CLK_OUT[3]/LCS[6]	W1	0	OV _{DD}	—
PCI_CLK_OUT[4]/LCS[7]	V3	0	OV _{DD}	—
PCI_SYNC_IN/PCI_CLOCK	U4	I	OV _{DD}	—
PCI_SYNC_OUT	U5	0	OV _{DD}	3
RTC/PIT_CLOCK	E9	I	OV _{DD}	—
CLKIN	W5	I	OV _{DD}	—
	JTAG		•	
ТСК	H27	I	OV _{DD}	_
TDI	H28	I	OV _{DD}	4
TDO	M24	0	OV _{DD}	3
TMS	J27	I	OV _{DD}	4
TRST	K26	I	OV _{DD}	4
	Test			
TEST	F28	I	OV _{DD}	6
TEST_SEL	Т3	I	OV _{DD}	6
	PMC	•	-	
QUIESCE	K27	0	OV _{DD}	—
	System Control			
PORESET	K28	I	OV _{DD}	—
HRESET	M25	I/O	OV _{DD}	1
SRESET	L27	I/O	OV _{DD}	2

System Design Information



21 System Design Information

This section provides electrical and thermal design recommendations for successful application of the MPC8347EA.

21.1 System Clocking

The MPC8347EA includes two PLLs:

- 1. The platform PLL generates the platform clock from the externally supplied CLKIN input. The frequency ratio between the platform and CLKIN is selected using the platform PLL ratio configuration bits as described in Section 19.1, "System PLL Configuration."
- 2. The e300 core PLL generates the core clock as a slave to the platform clock. The frequency ratio between the e300 core clock and the platform clock is selected using the e300 PLL ratio configuration bits as described in Section 19.2, "Core PLL Configuration."

21.2 PLL Power Supply Filtering

Each PLL gets power through independent power supply pins ($AV_{DD}1$, $AV_{DD}2$, respectively). The AV_{DD} level should always equal to V_{DD} , and preferably these voltages are derived directly from V_{DD} through a low frequency filter scheme.

There are a number of ways to provide power reliably to the PLLs, but the recommended solution is to provide four independent filter circuits as illustrated in Figure 43, one to each of the four AV_{DD} pins. Independent filters to each PLL reduce the opportunity to cause noise injection from one PLL to the other.

The circuit filters noise in the PLL resonant frequency range from 500 kHz to 10 MHz. It should be built with surface mount capacitors with minimum effective series inductance (ESL). Consistent with the recommendations of Dr. Howard Johnson in *High Speed Digital Design: A Handbook of Black Magic* (Prentice Hall, 1993), multiple small capacitors of equal value are recommended over a single large value capacitor.

To minimize noise coupled from nearby circuits, each circuit should be placed as closely as possible to the specific AV_{DD} pin being supplied. It should be possible to route directly from the capacitors to the AV_{DD} pin, which is on the periphery of package, without the inductance of vias.

Figure 43 shows the PLL power supply filter circuit.

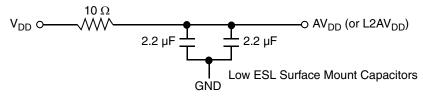


Figure 43. PLL Power Supply Filter Circuit

21.3 Decoupling Recommendations

Due to large address and data buses and high operating frequencies, the MPC8347EA can generate transient power surges and high frequency noise in its power supply, especially while driving large



 $OV_{DD}/2$. R_P then becomes the resistance of the pull-up devices. R_P and R_N are designed to be close to each other in value. Then, $Z_0 = (R_P + R_N) \div 2$.

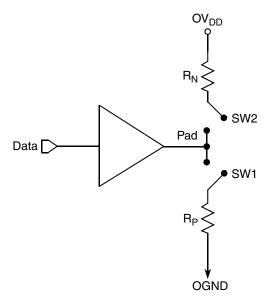


Figure 44. Driver Impedance Measurement

Two measurements give the value of this resistance and the strength of the driver current source. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term} . The measured voltage is $V_2 = (1 \div (1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1 \div V_2 - 1)$. The drive current is then $I_{source} = V_1 \div R_{source}$.

Table 69 summarizes the signal impedance targets. The driver impedance are targeted at minimum V_{DD} , nominal OV_{DD} , 105°C.

Impedance	Local Bus, Ethernet, DUART, Control, Configuration, Power Management	PCI Signals (Not Including PCI Output Clocks)	PCI Output Clocks (Including PCI_SYNC_OUT)	DDR DRAM	Symbol	Unit
R _N	42 Target	25 Target	42 Target	20 Target	Z ₀	W
R _P	42 Target	25 Target	42 Target	20 Target	Z ₀	W
Differential	NA	NA	NA	NA	Z _{DIFF}	W

Table 69. Impedance Characteristics

Note: Nominal supply voltages. See Table 1, $T_i = 105^{\circ}C$.

21.6 Configuration Pin Multiplexing

The MPC8347EA power-on configuration options can be set through external pull-up or pull-down resistors of 4.7 k Ω on certain output pins (see the customer-visible configuration pins). These pins are used as output only pins in normal operation.



Rev. Number	Date	Substantive Change(s)		
8	2/2009	 Added footnote 6 to Table 7. In Section 9.2, "USB AC Electrical Specifications," clarified that AC table is for ULPI only. In Table 39, corrected t_{LBKHOV} parameter to t_{LBKLOV} (output data is driven on falling edge of cloc in DLL bypass mode). Similarly, made the same correction to Figure 22, Figure 24, and Figure 2 for output signals. Added footnote 10 and 11 to Table 55 and Table 56. In Section 21.1, "System Clocking," removed "(AVDD1)" and "(AVDD2") from bulleted list. In Section 21.2, "PLL Power Supply Filtering," in the second paragraph, changed "provide five independent filter circuits," and "the five AVDD pins" to provide four independent filter circuits," an "the four AVDD pins." In Table 58, corrected the max csb_clk to 266 MHz. In Table 64, added PLL configurations 903, 923, A03, A23, and 503 for 533 MHz Added footnote 4 to Table 70. In Table 70, updated note 1 to say the following: "For temperature range = C, processor frequence is limited to 533 (TBGA) and 400 (PBGA) with a platform frequency of 266." 		
7	4/2007	 In Table 3, "Output Drive Capability," changed the values in the Output Impedance column and added USB to the seventh row. In Table 4, "Operating Frequencies for TBGA," added column for 400 MHz. In Section 21.7, "Pull-Up Resistor Requirements,"deleted last two paragraphs and after first paragraph, added a new paragraph. Deleted Section 21.8, "JTAG Configuration Signals," and Figure 43, "JTAG Interface Connection." 		
6	3/2007	 Page 1, updated first paragraph to reflect PowerQUICC II Pro information. In Table 18, "DDR and DDR2 SDRAM Input AC Timing Specifications," added note 2 to t_{CISKE} and deleted original note 3; renumbered the remaining notes. In Figure 43, "JTAG Interface Connection," updated with new figure. In Table 57, "Operating Frequencies for TBGA," in the 'Coherent system bus frequency (<i>csb_cl</i> row, changed the value in the 533 MHz column to 100-333. In Table 63, "Suggested PLL Configurations," under the subhead, '33 MHz CLKIN/PCI_CLK Options,' added row A03 between Ref. No. 724 and 804. Under the subhead '66 MHz CLKIN/PCI_CLK Options,' added row 503 between Ref. No. 305 and 404. For Ref. No. 306, changed the CORE PLL value to 0000110. In Section 23, "Ordering Information," replaced first paragraph and added a note. In Section 23.1, "Part Numbers Fully Addressed by this Document," replaced first paragraph. 		
5	1/2007	 In Table 1, "Absolute Maximum Ratings," added (1.36 max for 667-MHz core frequency). In Table 2, "Recommended Operating Conditions," added a row showing nominal core supply voltage of 1.3 V for 667-MHz parts. In Table 4, "MPC8347EA Power Dissipation," added two footnotes to 667-MHz row showing nominal core supply voltage of 1.3 V for 667-MHz parts. In Table 54, "MPC8347EA (TBGA) Pinout Listing," updated V_{DD} row to show nominal core supply voltage of 1.3 V for 667-MHz parts. 		
4	12/2006	Table 19, "DDR and DDR2 SDRAM Output AC Timing Specifications," modified T _{ddkhds} for 333 MHz from 900 ps to 775 ps.		
3	11/2006	 Updated note in introduction. In the features list in Section 1, "Overview," updated DDR data rate to show 266 MHz for PBGA parts for all silicon revisions, and 400 MHz for DDR2 for TBGA parts for silicon Rev. 2 and 3. In Table 5, "MPC8347EA Typical I/O Power Dissipation," added GV_{DD} 1.8-V values for DDR2; added table footnote to designate rates that apply only to the TBGA package. In Section 23, "Ordering Information," replicated note from document introduction. 		